Complementary 40 V, 6.0 A, Low $V_{CE(sat)}$ Transistor

NSS40302PDR2G

onsemi's e^2PowerEdge family of low $V_{CE(sat)}$ transistors are surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e^2PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25 °C)

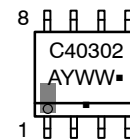| Rating		Symbol	Max	Unit
Collector-Emitter Voltage	NPN PNP	V_{CEO}	40 −40	Vdc
Collector-Base Voltage	NPN PNP	V_{CBO}	40 −40	Vdc
Emitter-Base Voltage	NPN PNP	V_{EBO}	6.0 −7.0	Vdc
Collector Current – Continuous	NPN PNP	I_C	3.0 −3.0	A
Collector Current – Peak	NPN PNP	I_{CM}	6.0 −6.0	A
Electrostatic Discharge		ESD	HBM Class 3B MM Class C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

COMPLEMENTARY LOW $V_{CE(sat)}$ TRANSISTOR EQUIVALENT $R_{DS(on)}$ 80 mΩ

COLLECTOR 7,8

COLLECTOR 5,6

2 BASE

4 BASE

1 EMITTER

3 EMITTER

8

1
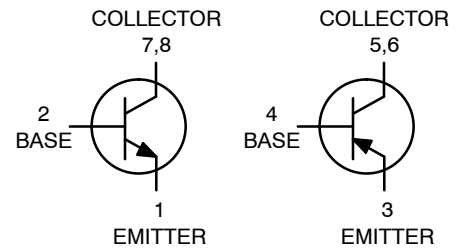
**SOIC-8
CASE 751
STYLE 16**

DEVICE MARKING

8

C40302
AYWW■

1

C40302	= Specific Device Code
A	= Assembly Location
Y	= Year
WW	= Work Week
■	= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping[†]
NSS40302PDR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NSV40302PDR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
SINGLE HEATED			
Total Device Dissipation (Note 1) T_A = 25 °C Derate above 25 °C	P_D	576 4.6	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	217	°C/W
Total Device Dissipation (Note 2) T_A = 25 °C Derate above 25 °C	P_D	676 5.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	185	°C/W
DUAL HEATED (Note 3)			
Total Device Dissipation (Note 1) T_A = 25 °C Derate above 25 °C	P_D	653 5.2	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	191	°C/W
Total Device Dissipation (Note 2) T_A = 25 °C Derate above 25 °C	P_D	783 6.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	160	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

1. FR-4 @ 10 mm^2, 1 oz. copper traces, still air.
2. FR-4 @ 100 mm^2, 1 oz. copper traces, still air.
3. Dual heated values assume total power is the sum of two equally powered devices.

NPN ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	–	–	Vdc
Collector-Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	40	–	–	Vdc
Emitter-Base Breakdown Voltage (I_E = 0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	–	–	Vdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0)	I_{CBO}	–	–	0.1	µAdc
Emitter Cutoff Current (V_{EB} = 6.0 Vdc)	I_{EBO}	–	–	0.1	µAdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) (I_C = 10 mA, V_{CE} = 2.0 V) (I_C = 500 mA, V_{CE} = 2.0 V) (I_C = 1.0 A, V_{CE} = 2.0 V) (I_C = 2.0 A, V_{CE} = 2.0 V)	h_{FE}	200 200 180 180	400 350 340 320	– – – –	
Collector-Emitter Saturation Voltage (Note 5) (I_C = 0.1 A, I_B = 0.010 A) (I_C = 1.0 A, I_B = 0.100 A) (I_C = 1.0 A, I_B = 0.010 A) (I_C = 2.0 A, I_B = 0.200 A)	$V_{CE(sat)}$	– – – –	0.008 0.044 0.080 0.082	0.011 0.060 0.115 0.115	V
Base-Emitter Saturation Voltage (Note 5) (I_C = 1.0 A, I_B = 0.01 A)	$V_{BE(sat)}$	–	0.780	0.900	V
Base-Emitter Turn-on Voltage (Note 5) (I_C = 0.1 A, V_{CE} = 2.0 V)	$V_{BE(on)}$	–	0.650	0.750	V
Cutoff Frequency (I_C = 100 mA, V_{CE} = 5.0 V, f = 100 MHz)	f_T	100	–	–	MHz
Input Capacitance (V_{EB} = 0.5 V, f = 1.0 MHz)	Cibo	–	320	450	pF
Output Capacitance (V_{CB} = 3.0 V, f = 1.0 MHz)	Cobo	–	40	50	pF
SWITCHING CHARACTERISTICS					
Delay (V_{CC} = 30 V, I_C = 750 mA, I_{B1} = 15 mA)	t_d	–	–	100	ns
Rise (V_{CC} = 30 V, I_C = 750 mA, I_{B1} = 15 mA)	t_r	–	–	100	ns
Storage (V_{CC} = 30 V, I_C = 750 mA, I_{B1} = 15 mA)	t_s	–	–	780	ns
Fall (V_{CC} = 30 V, I_C = 750 mA, I_{B1} = 15 mA)	t_f	–	–	110	ns

4. Pulsed Condition: Pulse Width = 300 µsec, Duty Cycle ≤ 2%.
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PNP ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector‑Emitter Breakdown Voltage (I_C = −10 mAdc, I_B = 0)	$V_{(BR)CEO}$	−40	–	–	Vdc
Collector‑Base Breakdown Voltage (I_C = −0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	−40	–	–	Vdc
Emitter‑Base Breakdown Voltage (I_E = −0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	−7.0	–	–	Vdc
Collector Cutoff Current (V_{CB} = −40 Vdc, I_E = 0)	I_{CBO}	–	–	−0.1	μAdc
Emitter Cutoff Current (V_{EB} = −6.0 Vdc)	I_{EBO}	–	–	−0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) (I_C = −10 mA, V_{CE} = −2.0 V) (I_C = −500 mA, V_{CE} = −2.0 V) (I_C = −1.0 A, V_{CE} = −2.0 V) (I_C = −2.0 A, V_{CE} = −2.0 V)	h_{FE}	250 220 180 150	380 340 300 230	– – – –	
Collector‑Emitter Saturation Voltage (Note 5) (I_C = −0.1 A, I_B = −0.010 A) (I_C = −1.0 A, I_B = −0.100 A) (I_C = −1.0 A, I_B = −0.010 A) (I_C = −2.0 A, I_B = −0.200 A)	$V_{CE(sat)}$	– – – –	−0.013 −0.075 −0.130 −0.135	−0.017 −0.095 −0.170 −0.170	V
Base‑Emitter Saturation Voltage (Note 5) (I_C = −1.0 A, I_B = −0.01 A)	$V_{BE(sat)}$	–	−0.780	−0.900	V
Base‑Emitter Turn‑on Voltage (Note 5) (I_C = −0.1 A, V_{CE} = −2.0 V)	$V_{BE(on)}$	–	−0.660	−0.750	V
Cutoff Frequency (I_C = −100 mA, V_{CE} = −5.0 V, f = 100 MHz)	f_T	100	–	–	MHz
Input Capacitance (V_{EB} = −0.5 V, f = 1.0 MHz)	Cibo	–	250	300	pF
Output Capacitance (V_{CB} = −3.0 V, f = 1.0 MHz)	Cobo	–	50	65	pF
SWITCHING CHARACTERISTICS					
Delay (V_{CC} = −30 V, I_C = −750 mA, I_{B1} = −15 mA)	t_d	–	–	60	ns
Rise (V_{CC} = −30 V, I_C = −750 mA, I_{B1} = −15 mA)	t_r	–	–	120	ns
Storage (V_{CC} = −30 V, I_C = −750 mA, I_{B1} = −15 mA)	t_s	–	–	400	ns
Fall (V_{CC} = −30 V, I_C = −750 mA, I_{B1} = −15 mA)	t_f	–	–	130	ns

5. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%.

NPN TYPICAL CHARACTERISTICS
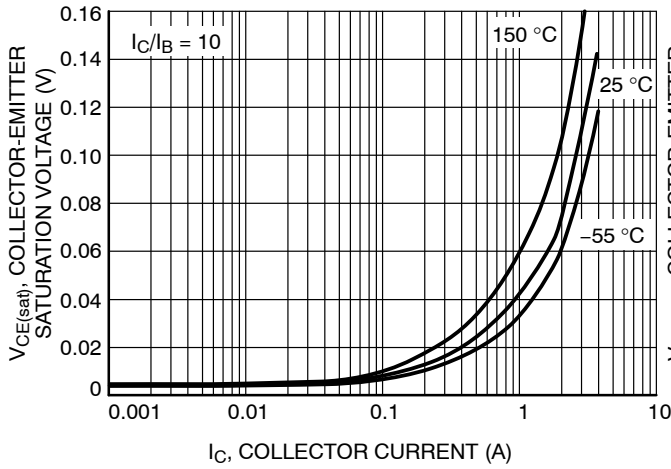
Figure 1. Collector Emitter Saturation Voltage vs. Collector Current
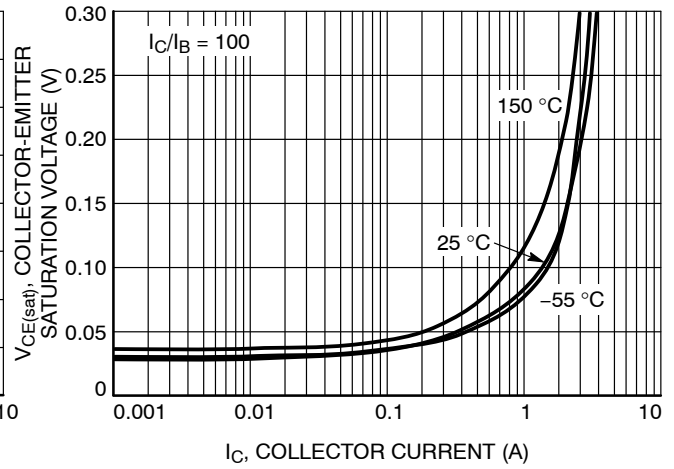
Figure 2. Collector Emitter Saturation Voltage vs. Collector Current
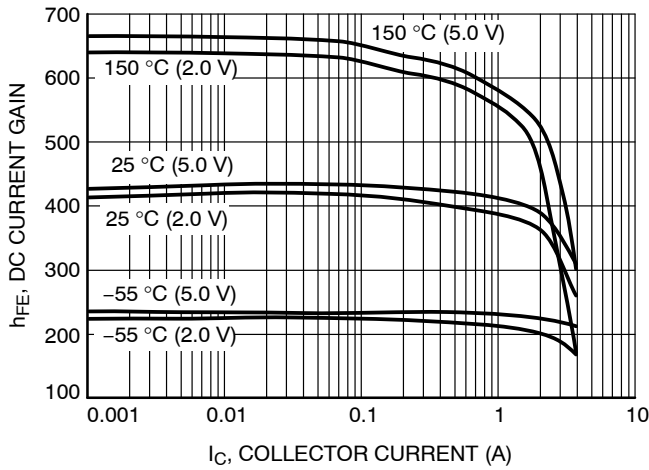
Figure 3. DC Current Gain vs. Collector Current
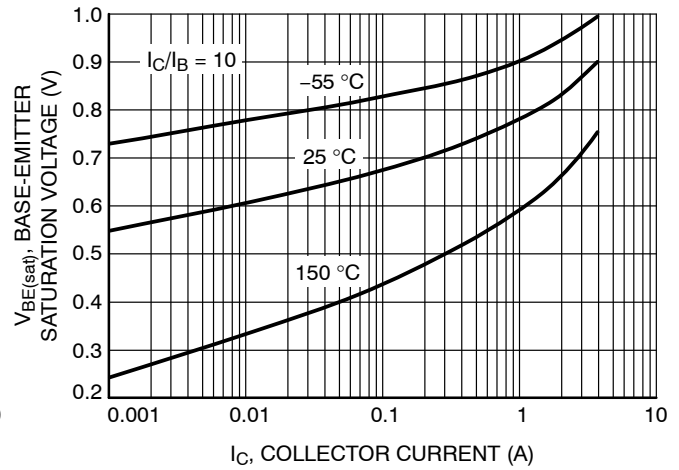
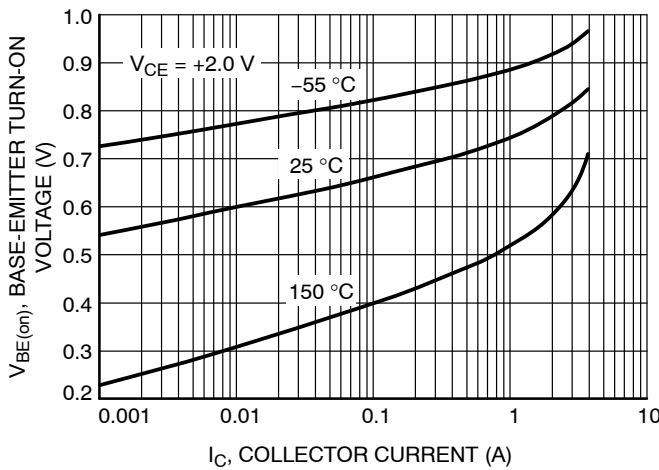**Figure 4. Base Emitter Saturation Voltage vs. Collector Current**

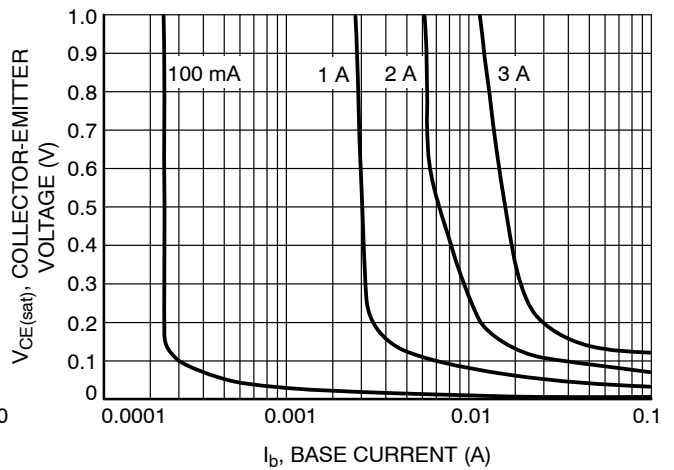**Figure 5. Base Emitter Turn-On Voltage vs. Collector Current**

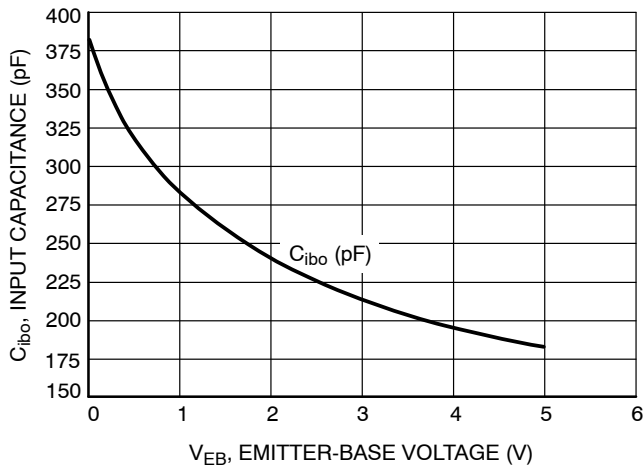**Figure 6. Saturation Region**
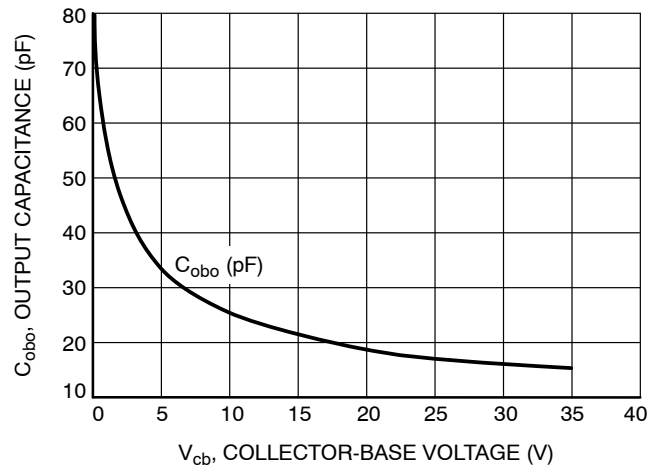
NPN TYPICAL CHARACTERISTICS
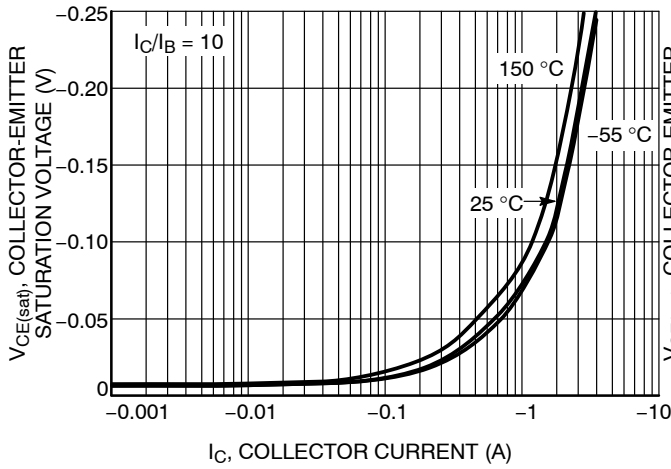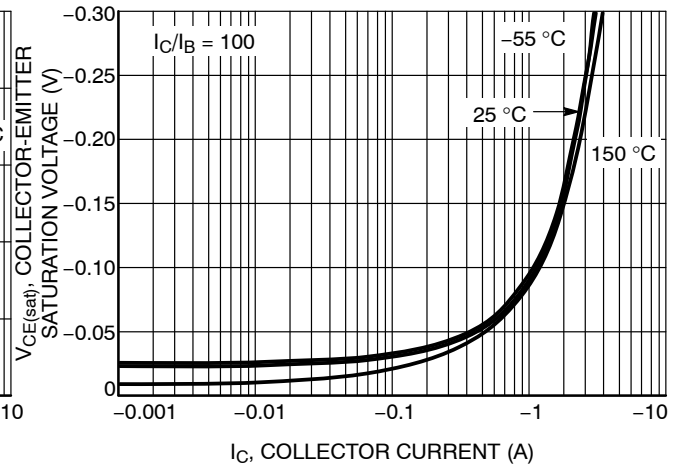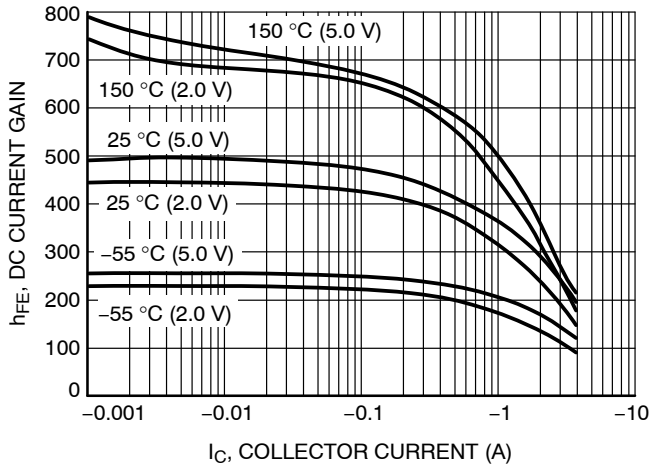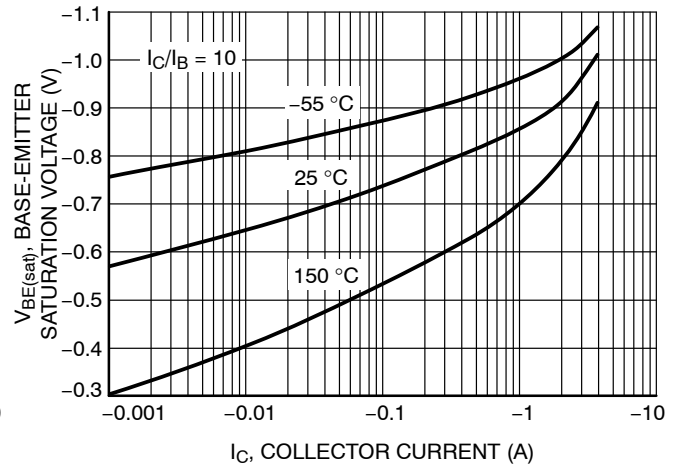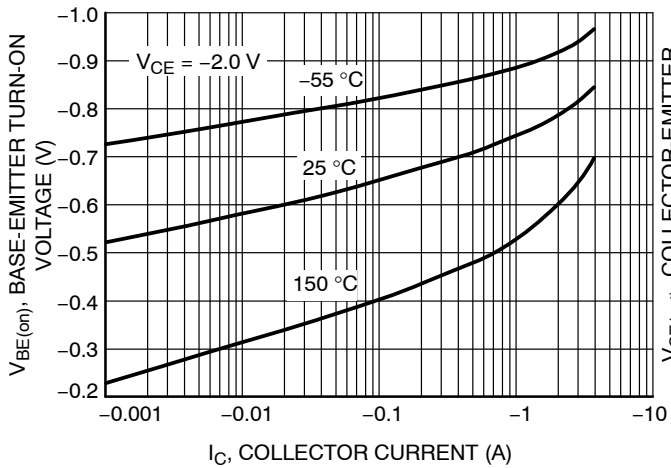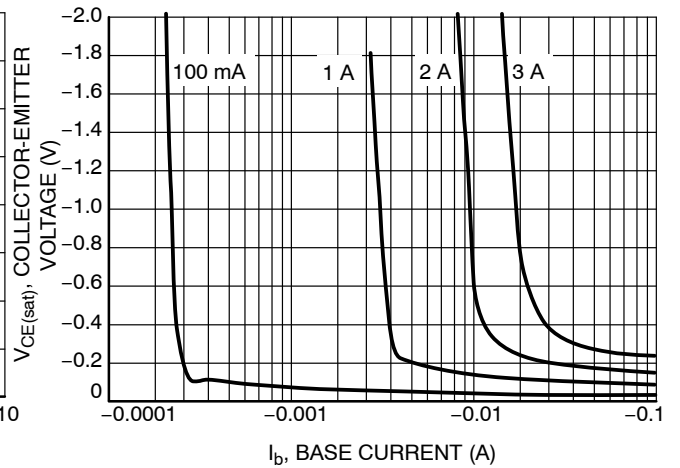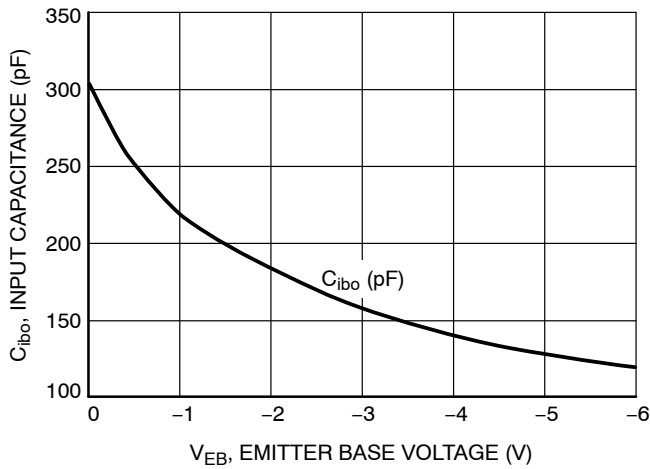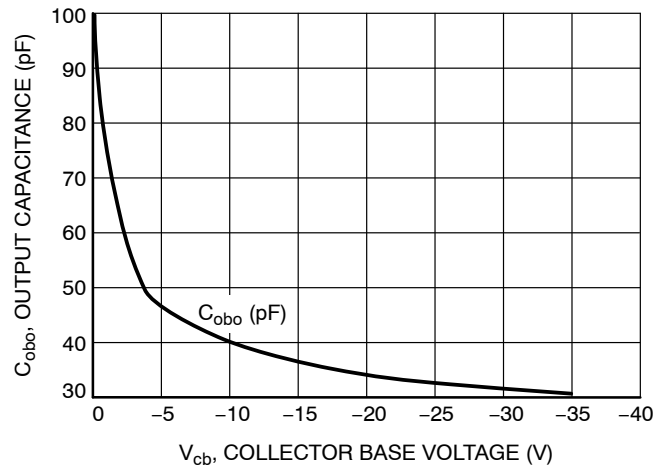

Figure 7. Input Capacitance

Figure 8. Output Capacitance
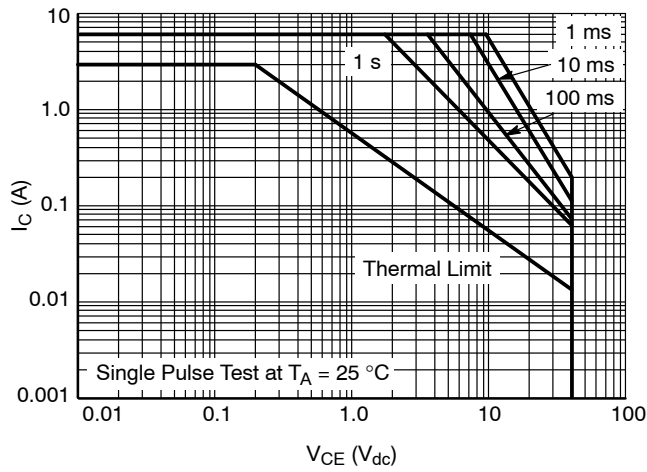

Figure 9. Safe Operating Area
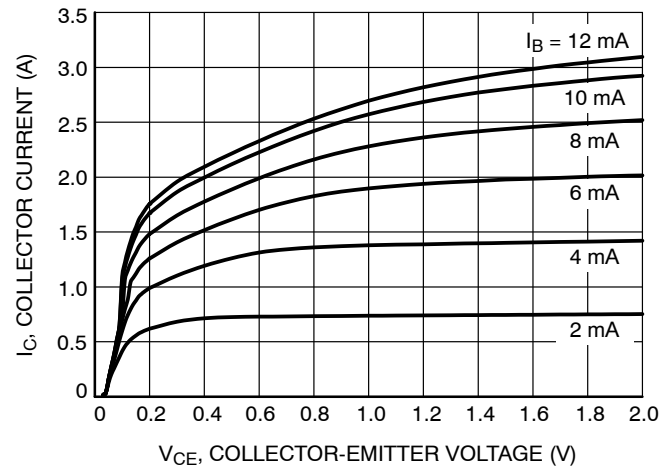
Figure 10. Collector Current as a Function of Collector Emitter Voltage

PNP TYPICAL CHARACTERISTICS

Figure 11. Collector Emitter Saturation Voltage
vs. Collector Current

Figure 12. Collector Emitter Saturation Voltage
vs. Collector Current

Figure 13. DC Current Gain vs. Collector
Current

Figure 14. Base Emitter Saturation Voltage vs.
Collector Current

Figure 15. Base Emitter Turn-On Voltage vs.
Collector Current

Figure 16. Saturation Region

PNP TYPICAL CHARACTERISTICS

Figure 17. Input Capacitance

Figure 18. Output Capacitance
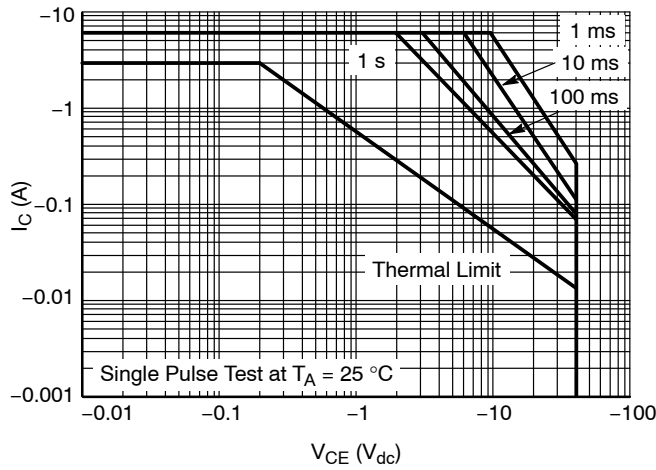
Figure 19. Safe Operating Area

Figure 20. Output Capacitance
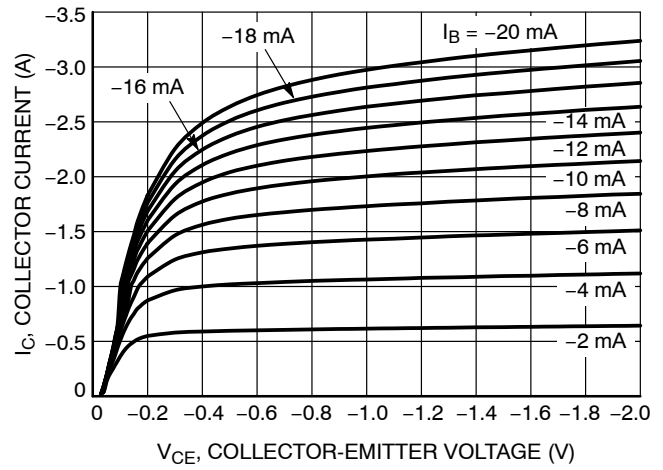
REVISION HISTORY

Revision	Description of Changes	Date
3	Rebranded the Data Sheet to **onsemi** format.	11/03/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.
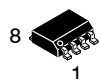
SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

8

1

SCALE 1:1
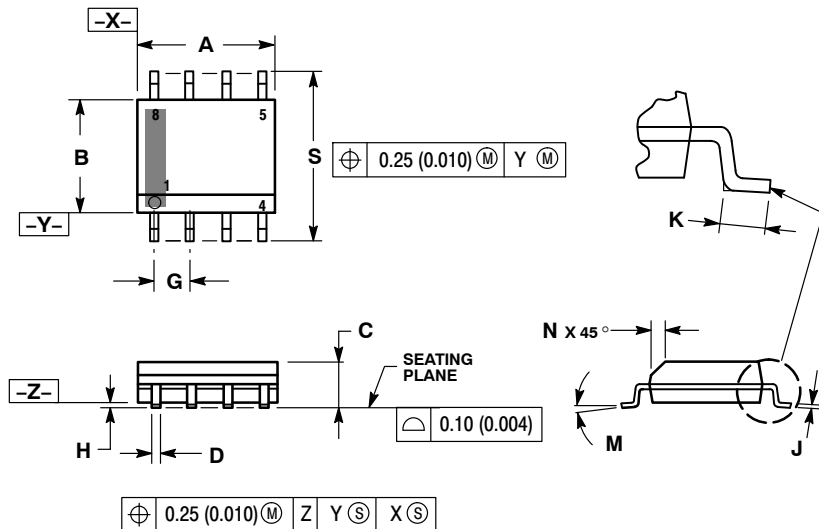
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

| $\oplus$ | 0.25 (0.010) Ⓜ | Y Ⓜ |

| ⌢ | 0.10 (0.004) |

| $\oplus$ | 0.25 (0.010) Ⓜ | Z Y Ⓢ X Ⓢ |

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*

1.52 / 0.060

7.0 / 0.275

4.0 / 0.155

0.6 / 0.024

1.270 / 0.050

SCALE 6:1 $\left(\dfrac{mm}{inches}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

8 — XXXXX ALYWX — 1
IC

8 — XXXXX ALYWX ▪ — 1
IC (Pb−Free)

8 — XXXXXX AYWW — 1
Discrete

8 — XXXXXX AYWW ▪ — 1
Discrete (Pb−Free)
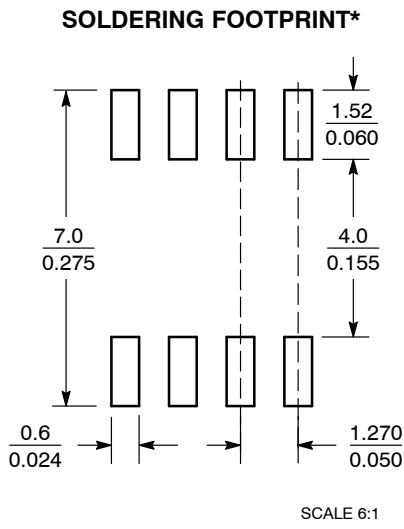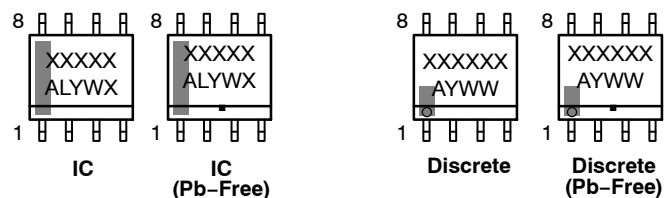
XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B		
DESCRIPTION:	SOIC−8 NB		**PAGE 1 OF 2**

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. BASE, #2
6. EMITTER, #2
7. BASE, #1
8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. GATE, #2
6. SOURCE, #2
7. GATE, #1
8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
7. ANODE
8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. DRAIN
5. GATE
6. GATE
7. SOURCE
8. SOURCE

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. DRAIN
4. SOURCE
5. SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 7:
PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
2. BASE, #1
3. BASE, #2
4. COLLECTOR, #2
5. COLLECTOR, #2
6. EMITTER, #2
7. EMITTER, #1
8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
2. COLLECTOR, DIE #1
3. COLLECTOR, DIE #2
4. EMITTER, COMMON
5. EMITTER, COMMON
6. BASE, DIE #2
7. BASE, DIE #1
8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND
5. GROUND
6. BIAS 2
7. INPUT
8. GROUND

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
2. N−GATE
3. P−SOURCE
4. P−GATE
5. P−DRAIN
6. P−DRAIN
7. N−DRAIN
8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
2. V2OUT
3. V1OUT
4. TXE
5. RXE
6. VEE
7. GND
8. ACC

STYLE 18:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3
4. CATHODE 4
5. CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
2. N/C
3. REXT
4. GND
5. IOUT
6. IOUT
7. IOUT
8. IOUT

STYLE 26:
PIN 1. GND
2. dv/dt
3. ENABLE
4. ILIMIT
5. SOURCE
6. SOURCE
7. SOURCE
8. VCC

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
2. DASIC_OFF
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
2. EMITTER, #1
3. BASE, #2
4. EMITTER, #2
5. COLLECTOR, #2
6. COLLECTOR, #2
7. COLLECTOR, #1
8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
6. SOURCE 1/DRAIN 2
7. SOURCE 1/DRAIN 2
8. GATE 1

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